ABSTRACT OF THE DISCLOSURE

A method of laser irradiation including: reflecting a linear laser beam from a mirror to bend an optical path of the laser beam, adjusting a width of the laser beam in the short axis direction of the laser beam whose optical path is bent by the mirror, by a short axis homogenizer, and irradiating an amorphous silicon semiconductor on a translucent substrate with the laser beam whose width in the short axis direction is adjusted by the short axis homogenizer, wherein the intensity of the laser beam is adjusted by adjusting the angle of the mirror.



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